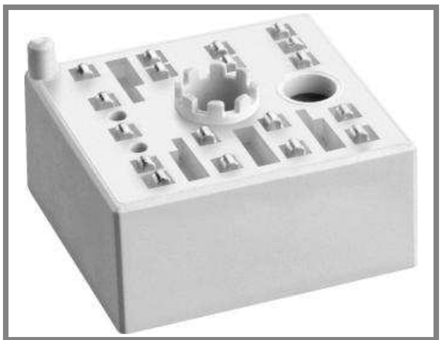
SKiiP 02NEB066V3 CONVERTER, INVERTER, BRAKE



MiniSKiiP®0

1-phase bridge rectifier + brake chopper + 3-phase bridge inverter

SKiiP 02NEB066V3

Absolute Maximum Ratings		T_S= 25°C, unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT - Inverter, Chopper			
V_{CES}		600	V
I_C	T_s = 25 (70) °C, T_j = 150 °C	19 (14)	A
I_C	T_s = 25 (70) °C, T_j = 175 °C	20 (16)	A
I_{CRM}	t_p = 1 ms	20	A
V_{GES}		±20	V
Diode - Inverter, Chopper			
I_F	T_s = 25 (70) °C, T_j = 150 °C	20 (15)	A
I_F	T_s = 25 (70) °C, T_j = 175 °C	20 (18)	A
I_{FRM}	t_p = 1 ms	20	A
Diode - Rectifier			
V_{RRM}		800	V
I_F	T_s = 70 °C	35	A
I_{FSM}	t_p = 10 ms, sin 180 °, T_j = 25 °C	220	A
i²t	t_p = 10 ms, sin 180 °, T_j = 25 °C	240	A²s
I_{tRMS}	per power terminal (20 A / spring)	20	A
T_j	IGBT, Diode	-40...+175	°C
T_{stg}		-40...+125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics				T_S= 25°C, unless otherwise specified	
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT - Inverter, Chopper					
$V_{CE(sat)}$	I_{Cnom} = 10 A, T_j = 25 (150) °C		1,45 (1,65)	1,85 (2,05)	V
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 1 mA		5,8		V
$V_{CE(TO)}$	T_j = 25 (150) °C		0,9 (0,7)	1,1 (1)	V
r_{CE}	T_j = 25 (150) °C		60 (100)	80 (110)	mΩ
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,58		nF
C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,12		nF
C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,04		nF
$R_{CC'+EE'}$	spring contact-chip T_s = 25 (150)°C				mΩ
$R_{th(j-s)}$	per IGBT		2		K/W
$t_{d(on)}$	under following conditions		25		ns
t_r	V_{CC} = 300 V, V_{GE} = ± 15 V		25		ns
$t_{d(off)}$	I_{Cnom} = 10 A, T_j = 150 °C		190		ns
t_f	R_{Gon} = R_{Goff} = 39 Ω		40		ns
E_{on} (E_{off})	inductive load		0,5 (0,3)		mJ
Diode - Inverter, Chopper					
V_F = V_{EC}	I_F = 10 A, T_j = 25 (150) °C		1,3 (1,3)	1,6 (1,6)	V
$V_{(TO)}$	T_j = 25 (150) °C		0,9 (0,8)	1 (0,9)	V
r_T	T_j = 25 (150) °C		40 (50)	60 (70)	mΩ
$R_{th(j-s)}$	per diode		2,46		K/W
I_{RRM}	under following conditions		15,8		A
Q_{rr}	I_{Fnom} = 10 A, V_R = 300 V		1,5		µC
E_{rr}	V_{GE} = 0 V, T_j = 150°C		0,5		mJ
	di_F/dt = 810 A/µs				
Diode - Rectifier					
V_F	I_{Fnom} = 15 A, T_j = 25 °C		1,1		V
$V_{(TO)}$	T_j = 150 °C		0,8		V
r_T	T_j = 150 °C		20		mΩ
$R_{th(j-s)}$	per diode		1,5		K/W
Temperature Sensor					
R_{ts}	3 %, T_r = 25 (100) °C		1000(1670)		Ω
Mechanical Data					
w			21,5		g
M_s	Mounting torque	2		2,5	Nm

Features

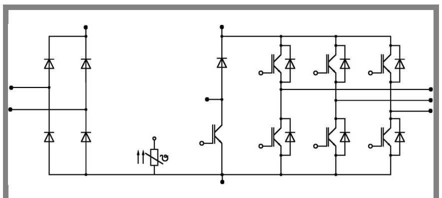
- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL reognised file no. E63532

Typical Applications*

- Inverter up to 5 kVA
- Typical motor power 2,2 kW

Remarks

- Case temperature limited to T_C= 125°C max.
- Product reliability results are valid for T_j= 150°C
- SC data: $t_p \leq 6$ µs; $V_{GE} \leq 15$ V; T_j = 150°C; V_{CC} = 360 V
- V_{CEsat} , V_F = chip level value



NEB

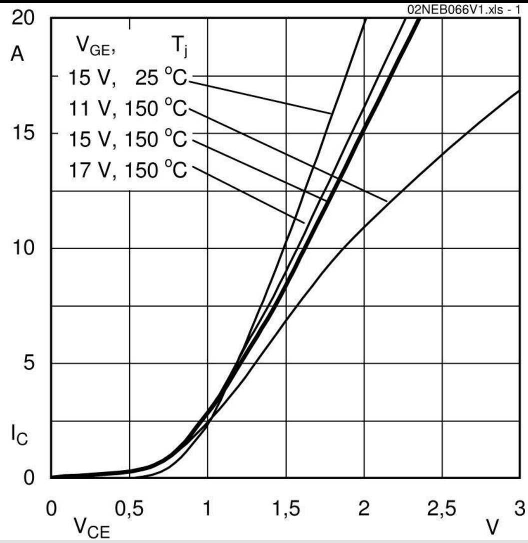


Fig. 1 Typ. output characteristic

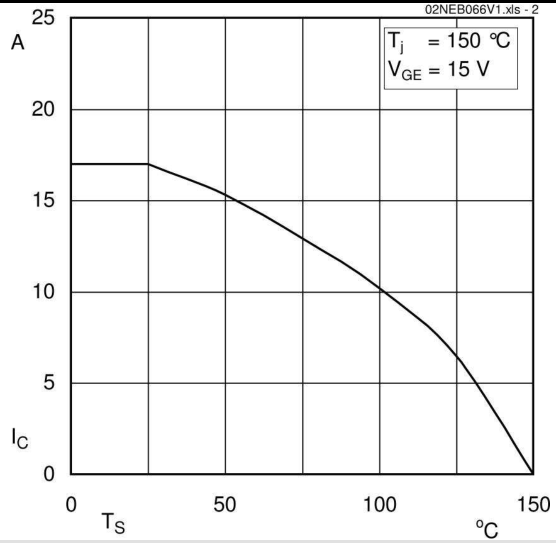


Fig. 2 Typ rated current vs. temperature

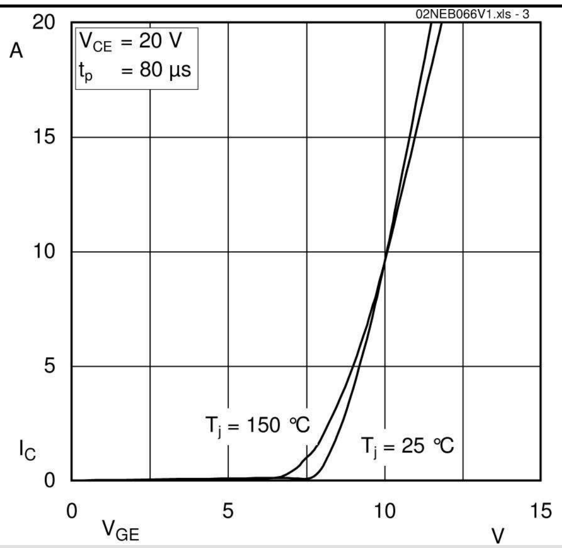


Fig. 3 Typ. transfer characteristic

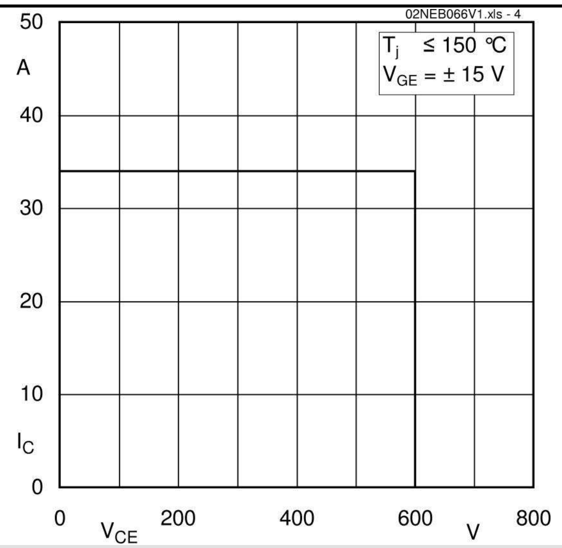


Fig. 4 Reverse bias safe operating area

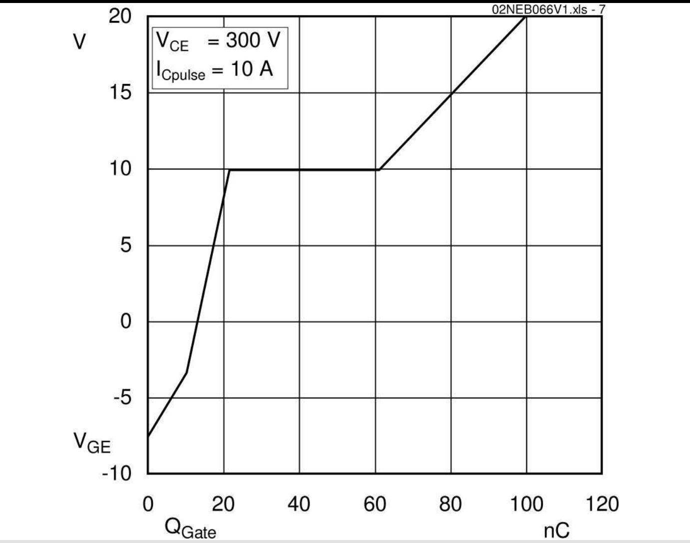


Fig. 7 Typ. gate charge characteristic

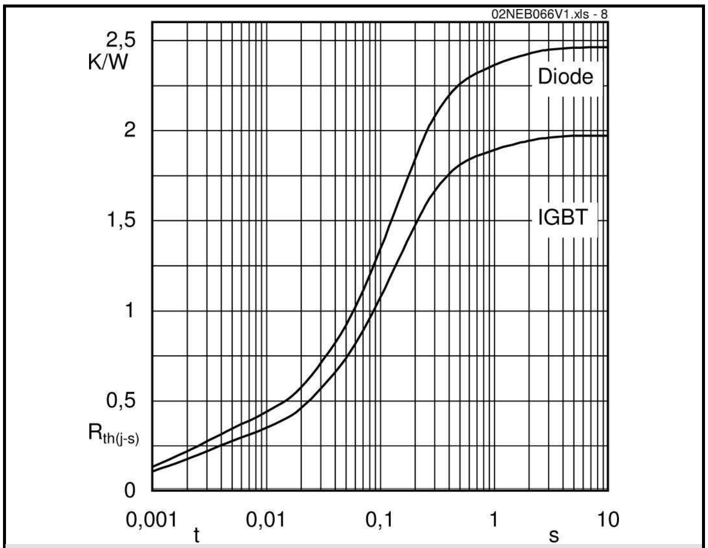


Fig. 8 Typ. thermal impedance

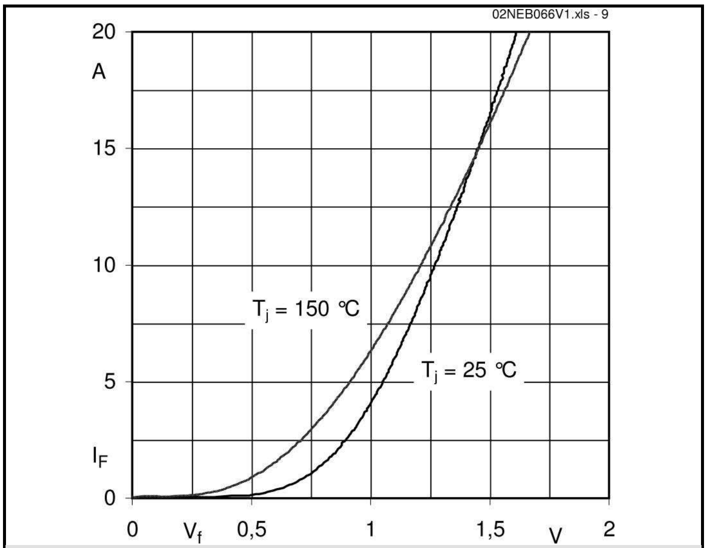


Fig. 9 Typ. freewheeling diode forward characteristic

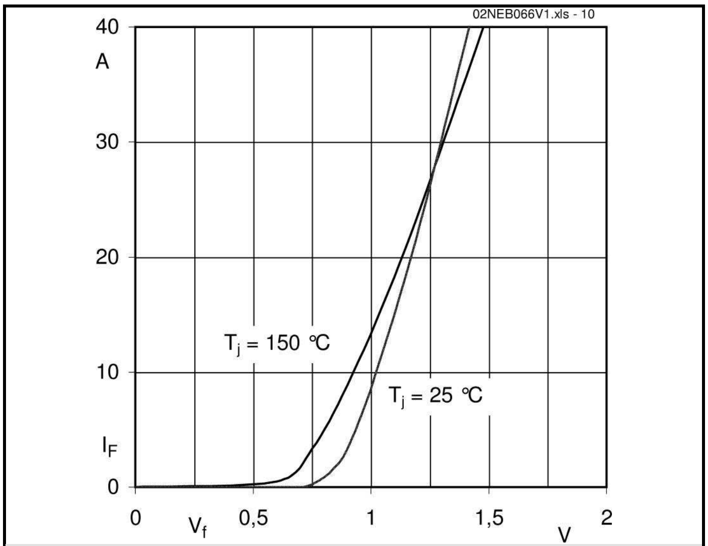
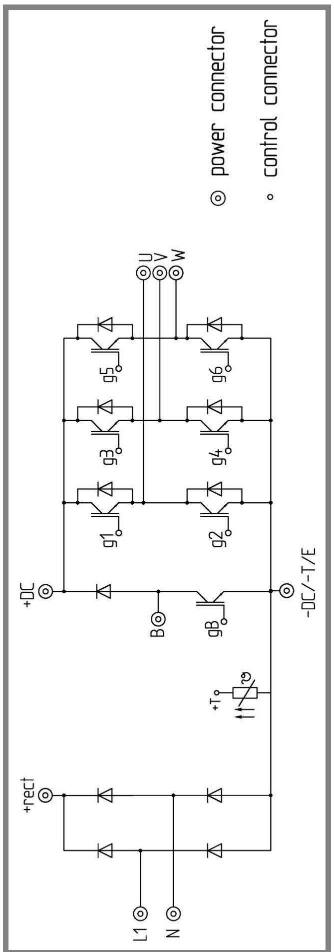
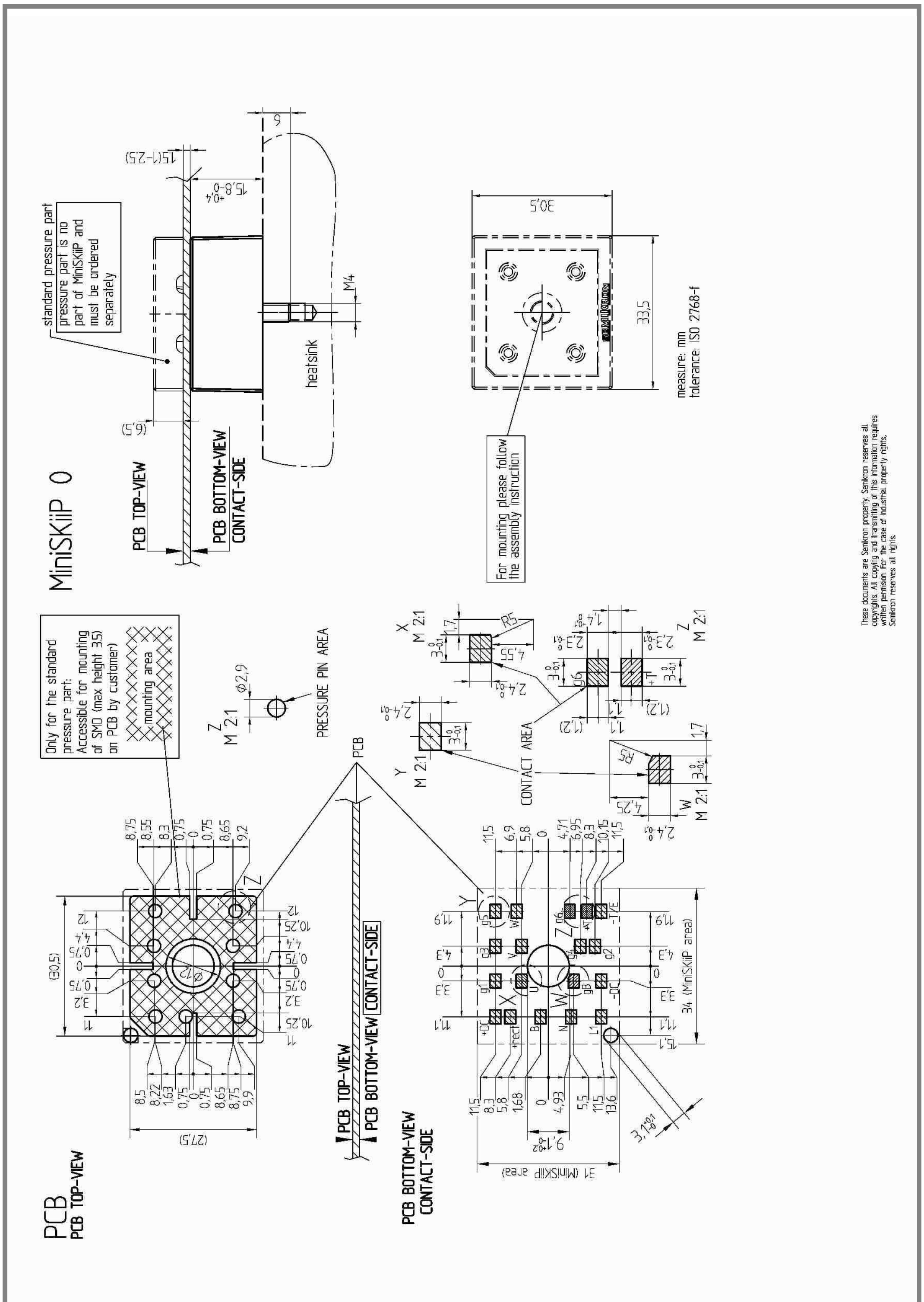


Fig. 10 Typ. input bridge forward characteristic



circuit



pinout, dimensions

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.